

## Supplementary Information

### Rubicene: A Molecular Fragment of C<sub>70</sub> for Use in Organic Field-Effect Transistors

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Figure S1, Lee *et al.*

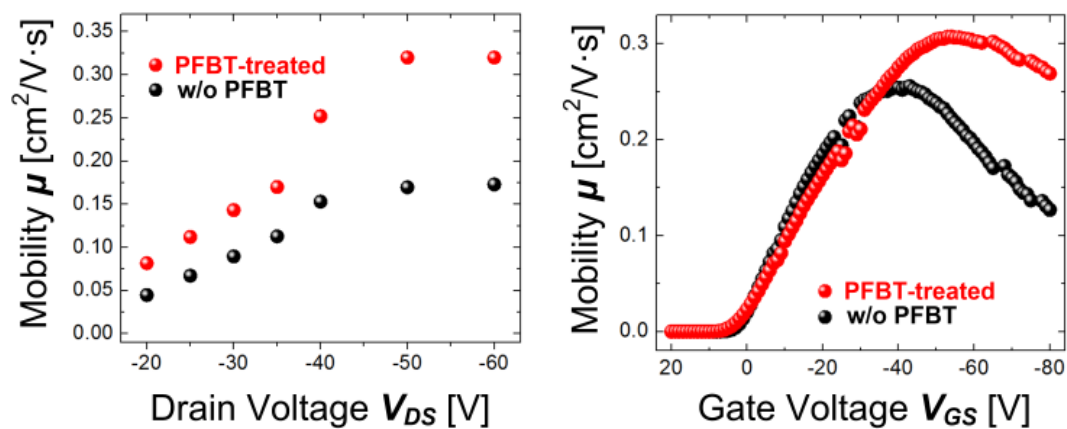


Figure S1. The plot of dependence of the mobility on (a) source-drain voltage ( $V_{DS}$ ) and (b) gate voltage ( $V_{GS}$ ) calculated using the expression  $\mu = (2L/WC_i)(\partial I_{DS}^{1/2}/\partial V_{GS})^2$ .

Figure S2, Lee *et al.*

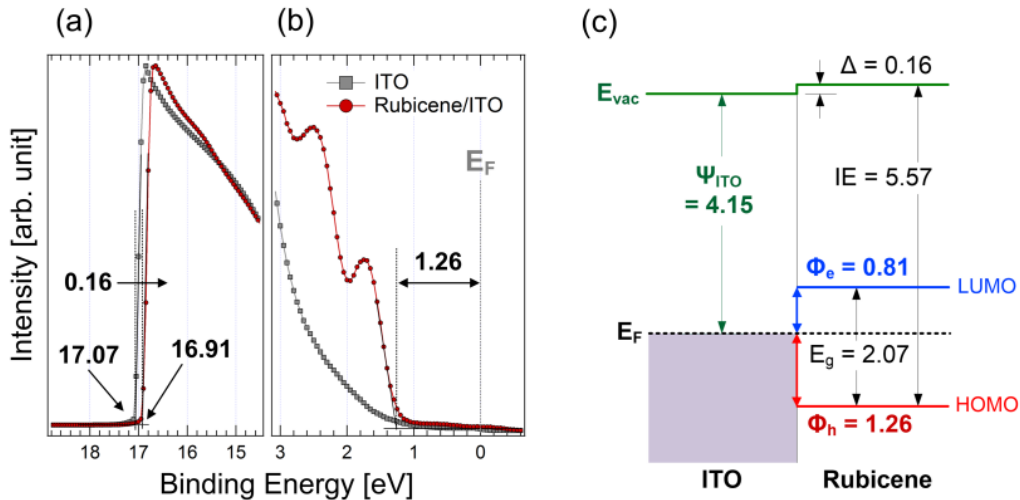


Figure S2. The measured UPS spectra of (a) the secondary electron cutoff (SEC) region and (b) the HOMO region of rubicene (6.0 nm)/ITO and (c) the energy level diagram of rubicene/ITO. Each spectrum is normalized in the SEC region and the Shirley-type of background is removed from the HOMO region spectra for clear comparison.